

STD5NM60 STB8NM60 - STP8NM60

N-channel 650 V@Tjmax, 0.9 Ω, 8 A MDmesh™ Power MOSFET TO-220, TO-220FP, D²PAK, DPAK, IPAK

Features

Туре	V _{DSS}	R _{DS(on)}	I _D	Pw
STD5NM60	650 V	<1Ω	5 A	96 W
STD5NM60-1	650 V	< 1 Ω	5 A	96 W
STB8NM60	650 V	< 1 Ω	5 A	100 W
STP8NM60	650 V	< 1 Ω	8 A	100 W
STP8NM60FP	650 V	< 1 Ω	8 A ⁽¹⁾	30 W

- 100% avalanche tested
- HIgh dv/dt and avalanche capabilities
- Low input capacitance and gate charge
- Low gate input resistance



■ Switching applications

Description

The MDmesh[™] is a new revolutionary Power MOSFET technology that associates the multiple drain process with the company's PowerMESH[™] horizontal layout. The resulting product has an outstanding low on-resistance, impressively high dv/dt and excellent avalanche characteristics. The adoption of the company's proprietary strip technique yields overall dynamic performance that is significantly better than that of similar competition's products.

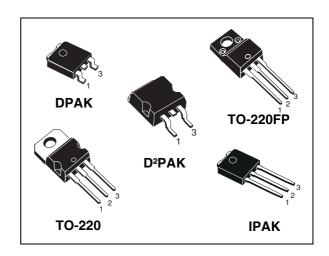


Figure 1. Internal schematic diagram

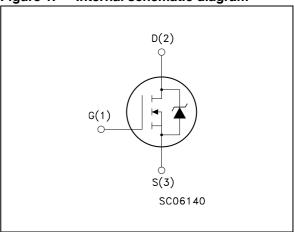


Table 1. Device summary

Order codes	Marking	Package	Packaging
STD5NM60-1	D5NM60	IPAK	Tube
STD5NM60T4	D5NM60	DPAK	Tape & reel
STB8NM60T4	B8NM60	D ² PAK	Tape & reel
STP8NM60	P8NM60	TO-220	Tube
STP8NM60FP	P8NM60FP	TO-220FP	Tube

October 2008 Rev 17 1/18

1 Electrical ratings

Table 1. Absolute maximum ratings

			Value		
Symbol	Parameter	TO-220 D²PAK	TO-220FP	IPAK DPAK	Unit
V _{GS}	Gate-source voltage		± 30		V
I _D	Drain current (continuous) at T _C = 25 °C	8	8 ⁽¹⁾	5	Α
I _D	Drain current (continuous) at T _C =100 °C	5	5 ⁽¹⁾	3.1 ⁽¹⁾	Α
I _{DM} ⁽²⁾	Drain current (pulsed)	32	32 ⁽¹⁾	20 (1)	Α
P _{TOT}	Total dissipation at T _C = 25 °C	100	30	96	W
	Derating factor	0.8	0.24	0.0.4	W/°C
dv/dt ⁽³⁾	Peak diode recovery voltage slope		15		V/ns
V _{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink (t=1 s;T _C =25 °C)		2500		V
T _J T _{stg}	Operating junction temperature Storage temperature		-55 to 150		°C

^{1.} Limited only by maximum temperature allowed

Table 2. Thermal resistance

			Value		
Symbol	Parameter	TO-220 D²PAK	IPAK DPAK	TO-220FP	Unit
R _{thj-case}	Thermal resistance junction-case max	1.25	4.16	°C/W	
R _{thj-a}	Thermal resistance junction-ambient max		62.5		°C/W
T _I	Maximum lead temperature for soldering purpose	300		°C	

Table 3. Avalanche data

Symbol	Parameter	Value	Unit
I _{AS}	Avalanche current, repetitive or not-repetitive (pulse width limited by Tj Max)	2.5	Α
E _{AS}	Single pulse avalanche energy (starting Tj=25 °C, I _D =I _{AS} , V _{DD} =50 V)	200	mJ

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^{2.} Pulse width limited by safe operating area

^{3.} $I_{SD} \leq$ 5 A, di/dt \leq 400 A/ μ s, V_{DD} = 80% $V_{(BR)DSS}$

2 Electrical characteristics

(T_{CASE} = 25 °C unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V _{(BR)DSS}	Drain-source breakdown voltage	$I_D = 250 \ \mu\text{A}, \ V_{GS} = 0$				V
I _{DSS}	Zero gate voltage drain current (V _{GS} = 0)	V_{DS} = max rating, V_{DS} = max rating @125 °C			1 10	μ Α μ Α
I _{GSS}	Gate body leakage current (V _{DS} = 0)	V _{GS} = ±20 V			±100	nA
V _{GS(th)}	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	3	4	5	V
R _{DS(on)}	Static drain-source on resistance	V_{GS} = 10 V, I_{D} = 2.5 A		0.9	1	Ω

Table 5. Dynamic

Symbol	Parameter	Parameter Test conditions		Тур.	Max.	Unit
9 _{fs}	Forward transconductance	$V_{DS} = I_{D(on)} \times R_{DS(on)max},$ $I_{D} = 2.5 \text{ A}$		2.4		s
C _{iss} C _{oss} C _{rss}	Input capacitance Output capacitance Reverse transfer capacitance	V _{DS} = 25 V, f=1 MHz, V _{GS} =0		400 100 10		pF pF pF
C _{oss eq} ⁽¹⁾ .	Equivalent output capacitance	V _{GS} =0, V _{DS} =0 to 480 V		50		pF
Q _g Q _{gs} Q _{gd}	Total gate charge Gate-source charge Gate-drain charge	V_{DD} = 400 V, I_{D} = 5 A V_{GS} =10 V (see Figure 12)		13 5 6	18	nC nC nC

C_{oss eq.} is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
t _{d(on)} t _r t _{d(off)} t _f	Turn-on delay time Rise time Turn-off delay time Fall time	V_{DD} = 300 V, I_{D} = 2.5 A, R_{G} = 4.7 Ω , V_{GS} =10 V (see Figure 17)		14 10 23 10		ns ns ns
t _{r(Voff)} t _f t _c	Off-voltage rise time Fall time Cross-over time	V_{DD} = 480 V, I_{D} = 5 A, R_{G} = 4.7 Ω , V_{GS} =10 V		7 10 17		ns ns ns

Table 7. Source drain diode

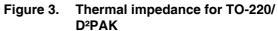
Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I _{SD}	Source-drain current				8	Α
I _{SDM} ⁽¹⁾	Source-drain current (pulsed)				32	Α
V _{SD} ⁽²⁾	Forward on voltage	I _{SD} = 5A, V _{GS} =0			1.5	V
t _{rr} Q _{rr}	Reverse recovery time Reverse recovery charge	$I_{SD} = 5 \text{ A}, V_{DD} = 100 \text{ V}$ di/dt = 100 A/ μ s,		300 1.95		ns μC
I _{RRM}	Reverse recovery current	(see Figure 22)		13		Α
t _{rr} Q _{rr} I _{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 5 \text{ A}, V_{DD} = 100 \text{ V}$ di/dt = 100 A/ μ s, Tj=150 °C (see Figure 22)		445 3.00 13.5		ns μC Α

^{1.} Pulse width limited by safe operating area

^{2.} Pulsed: pulse duration=300µs, duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for TO-220/ D²PAK



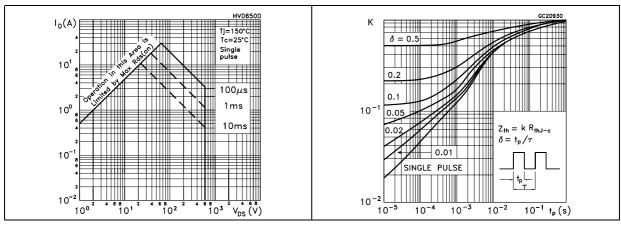


Figure 4. Safe operating area for TO-220FP

Figure 5. Thermal impedance for TO-220FP

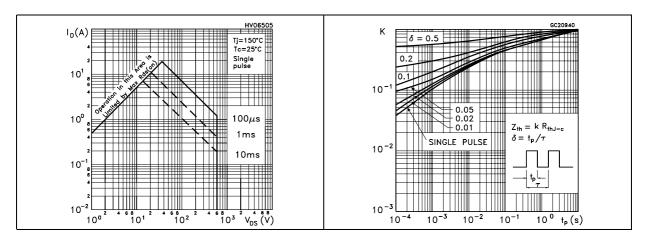
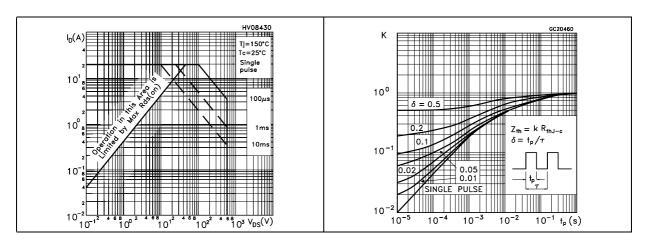


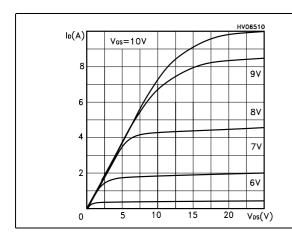
Figure 6. Safe operating area for DPAK/IPAK Figure 7. Thermal impedance for DPAK/IPAK



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Figure 8. Output characteristics

Figure 9. Transfer characteristics



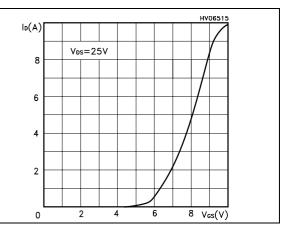
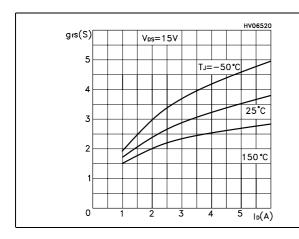


Figure 10. Transconductance

Figure 11. Static drain-source on resistance



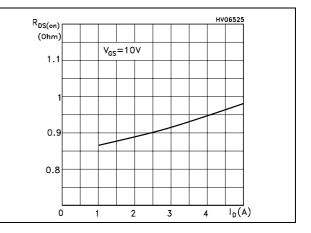
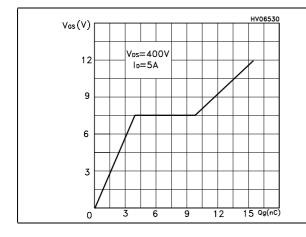


Figure 12. Gate charge vs gate-source voltage Figure 13. Capacitance variations



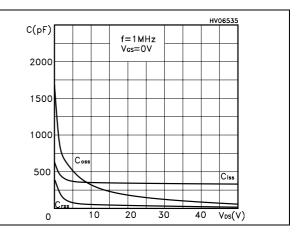
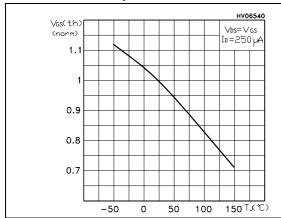


Figure 14. Normalized gate threshold voltage Figure 15. Normalized on resistance vs vs temperature temperature



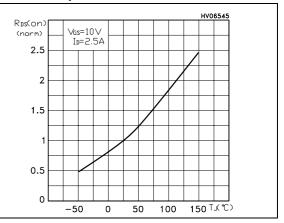
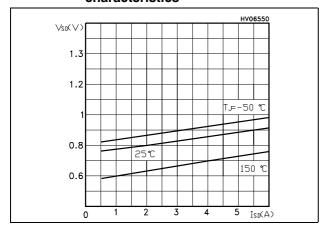


Figure 16. Source-drain diode forward characteristics



3 Test circuit

Figure 17. Switching times test circuit for resistive load

Figure 18. Gate charge test circuit

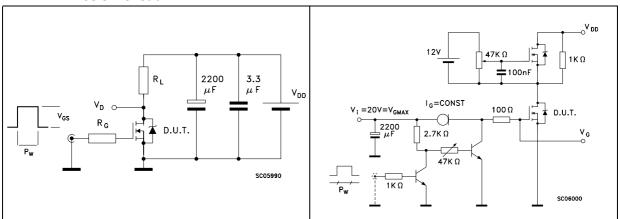


Figure 19. Test circuit for inductive load switching and diode recovery times

Figure 20. Unclamped inductive load test circuit

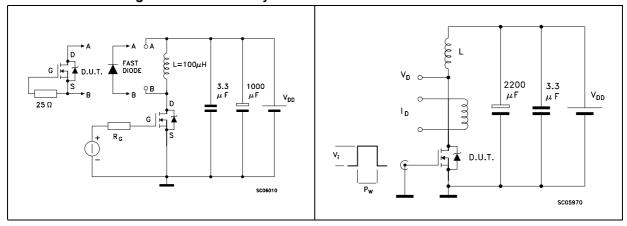
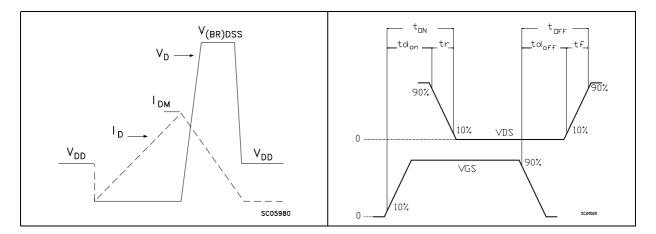


Figure 21. Unclamped inductive waveform

Figure 22. Switching time waveform



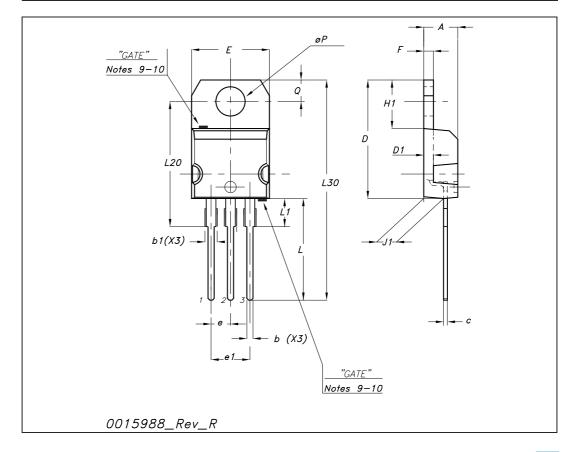
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4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

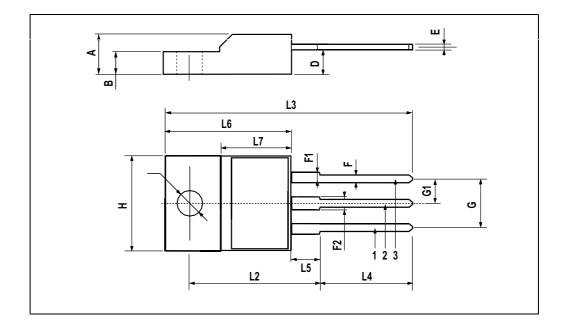
TO-220 mechanical data

Dim		mm			inch	
Dim	Min	Тур	Max	Min	Тур	Max
А	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
С	0.48		0.70	0.019		0.027
D	15.25		15.75	0.6		0.62
D1		1.27			0.050	
Е	10		10.40	0.393		0.409
е	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.051
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
ØP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



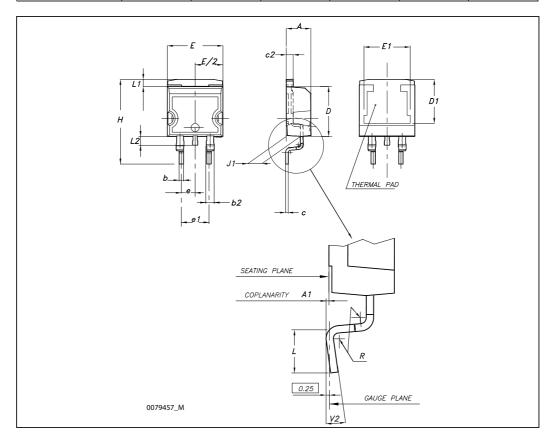
TO-220FP MECHANICAL DATA

DIM.		mm.			inch	
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
Α	4.4		4.6	0.173		0.181
В	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
Е	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
Н	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	.0385		0.417
L5	2.9		3.6	0.114		0.141
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



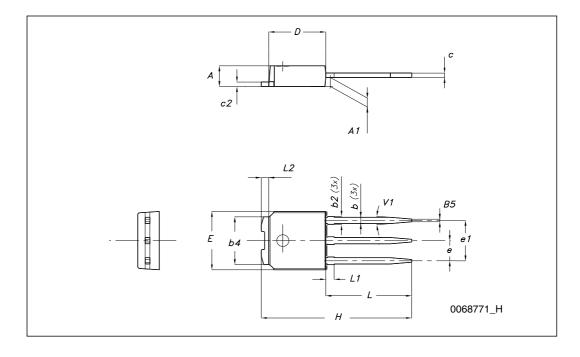
D²PAK (TO-263) mechanical data

Di		mm			inch	
Dim	Min	Тур	Max	Min	Тур	Max
Α	4.40		4.60	0.173		0.181
A1	0.03		0.23	0.001		0.009
b	0.70		0.93	0.027		0.037
b2	1.14		1.70	0.045		0.067
С	0.45		0.60	0.017		0.024
c2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1	7.50			0.295		
E	10		10.40	0.394		0.409
E1	8.50			0.334		
е		2.54			0.1	
e1	4.88		5.28	0.192		0.208
Н	15		15.85	0.590		0.624
J1	2.49		2.69	0.099		0.106
L	2.29		2.79	0.090		0.110
L1	1.27		1.40	0.05		0.055
L2	1.30		1.75	0.051		0.069
R		0.4			0.016	
V2	0°		8°	0°		8°



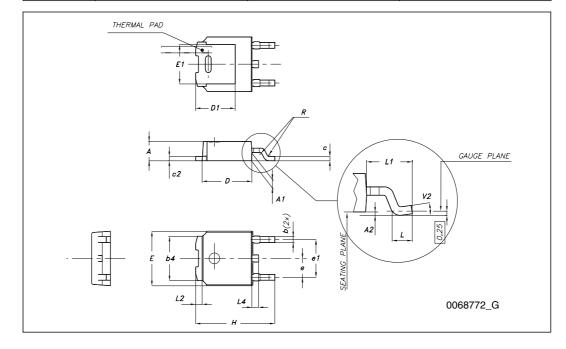
TO-251 (IPAK) mechanical data

DIM	mm.			
DIM.	min.	typ	max.	
Α	2.20		2.40	
A1	0.90		1.10	
b	0.64		0.90	
b2			0.95	
b4	5.20		5.40	
С	0.45		0.60	
c2	0.48		0.60	
D	6.00		6.20	
E	6.40		6.60	
е		2.28		
e1	4.40		4.60	
Н		16.10		
L	9.00		9.40	
(L1)	0.80		1.20	
L2		0.80		
V1		10 °		



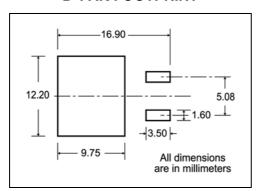
TO-252 (DPAK) mechanical data

DIM.	mm.			
DIIVI.	min.	typ	max.	
A	2.20		2.40	
A1	0.90		1.10	
A2	0.03		0.23	
b	0.64		0.90	
b4	5.20		5.40	
С	0.45		0.60	
c2	0.48		0.60	
D	6.00		6.20	
D1		5.10		
E	6.40		6.60	
E1		4.70		
е		2.28		
e1	4.40		4.60	
Н	9.35		10.10	
L	1			
L1		2.80		
L2		0.80		
L4	0.60		1	
R		0.20		
V2	0 °		8 °	

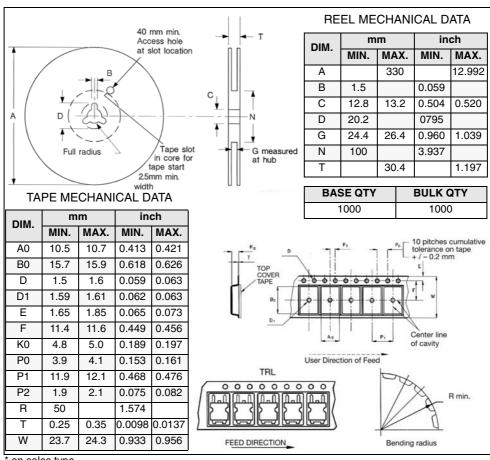


5 Packaging mechanical data

D²PAK FOOTPRINT

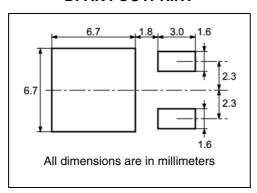


TAPE AND REEL SHIPMENT

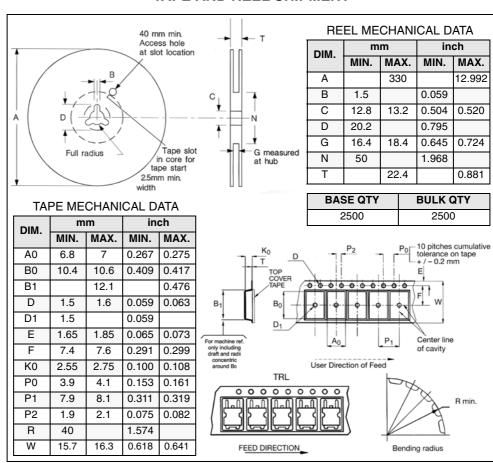


^{*} on sales type

DPAK FOOTPRINT



TAPE AND REEL SHIPMENT



6 Revision history

Table 8. Document revision history

Date	Revision	Changes
14-Apr-2004	11	Title changed
11-Apr-2005	12	Inserted D ² PAK
21-Feb-2006	13	New template
08-Sep-2006	14	Modified order codes
14-Sep-2006	15	Corrected Figure 6.: Safe operating area for DPAK/IPAK
09-Jul-2007	16	Qrr value in Table 7.: Source drain diode has been updated
01-Oct-2008	17	4: Package mechanical data updated

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